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QUAD-BAND GSM850/GSM900/DCS/PCS POWER AMP MODULE

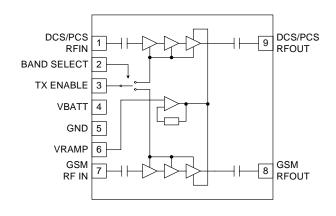
RoHS Compliant and Pb-Free Product Package Style: Module, 6mmx6mm

Features

- Ultra-Small, Ultra-Thin 6mmx6mmx1mm Package Size
- Integrated V_{RFG}
- Complete Power Control Solution
- Large Signal Polar Modulation EDGE Compatible
- No External Components or Routing
- Improved Power Flatness through Integrated Current Limiter. 2.5 A Maximum Current Draw over VSWR, all Phase Angles.

Applications

- 3V Quad-Band GSM and EDGE Handsets
- EDGE Capable Large Signal Polar Modulation Handsets
- Portable Battery-Powered Equipment
- GSM850/EGSM900/DCS/PC S Products
- GPRS Class 12
- Power Star[™] Module



Functional Block Diagram

Product Description

The RF3161 is a high-power, high-efficiency power amplifier module with integrated power control that provides over 50 dB of control range. The device is a self-contained $6\,\text{mm}\,\text{x}\,6\,\text{mm}\,\text{x}\,1\,\text{mm}$ module with $50\,\Omega$ input and output terminals. The device is designed for use as the final RF amplifier in GSM850, EGSM900, DCS and PCS handheld digital cellular equipment and other applications in the 824 MHz to 849 MHz, 880 MHz to 915 MHz, 1710 MHz to 1785 MHz and 1850 MHz to 1910 MHz bands. The RF3161 can be used for GSM and Polar Mod EDGE applications. The RF3161 requires no external routing or external components, simplifying layout and reducing board space.

Ordering Information

RF3161 Quad-Band GSM850/GSM900/DCS/PCS Power amp Module

RF3161 SB Power Amp Module 5-Piece Sample Pack RF3161PCBA-410 Fully Assembled Evaluation Board

Optimum Technology Matching® Applied

☐ GaAs HBT ☐ SiGe BiCMOS ☐ GaAs pHEMT ☐ GaN HE☐ GaAs MESFET ☐ Si BiCMOS ☐ Si CMOS ☐ InGaP HBT ☐ SiGe HBT ☐ Si BJT	aAs MESFET 🔲 S	Si BiCMOS	▼ Si CMOS	☐ GaN HEMT
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Please contact RFMD Technical Support at (336) 678-5570 for more information.